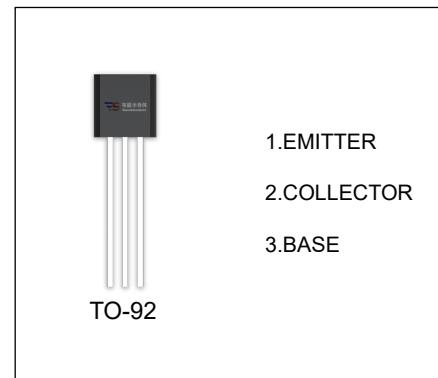


2N4402 TRANSISTOR (PNP)

FEATURES

- General Purpose Amplifier Transistor



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2N4402	TO-92	Bulk	1000pcs/Bag
2N4402-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_c	Collector Current -Continuous	-0.6	A
P_D	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$

T_a=25 °C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.1mA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.1mA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-40V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.1	μA
DC current gain	h _{FE} [*]	V _{CE} =-1V, I _C =-1mA	30			
		V _{CE} =-1V, I _C =-10mA	50			
		V _{CE} =-2V, I _C =-150mA	50		150	
		V _{CE} =-2V, I _C =-500mA	20			
Collector-emitter saturation voltage	V _{CE(sat)} [*]	I _C =-150mA, I _B =-15mA			-0.4	V
		I _C =-500mA, I _B =-50mA			-0.75	V
Base-emitter saturation voltage	V _{BE(sat)} [*]	I _C =-150mA, I _B =-15mA	-0.75		-0.95	V
		I _C =-500mA, I _B =-50mA			-1.3	V
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			8.5	pF
Emitter input capacitance	C _{ib}	V _{EB} =-0.5V, I _C =0, f=1MHz			30	pF
Transition frequency	f _T	V _{CE} =-10V, I _C =-20mA, f=100MHz	150			MHz

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.